



ECH8653

N-Channel Power MOSFET 20V, 7.5A, 20mΩ, Dual ECH8

ON Semiconductor®

<http://onsemi.com>

Features

- Low ON-resistance
- Best suited for LiB charging and discharging switch
- Halogen free compliance
- 4V drive
- Common-drain type
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta=25°C

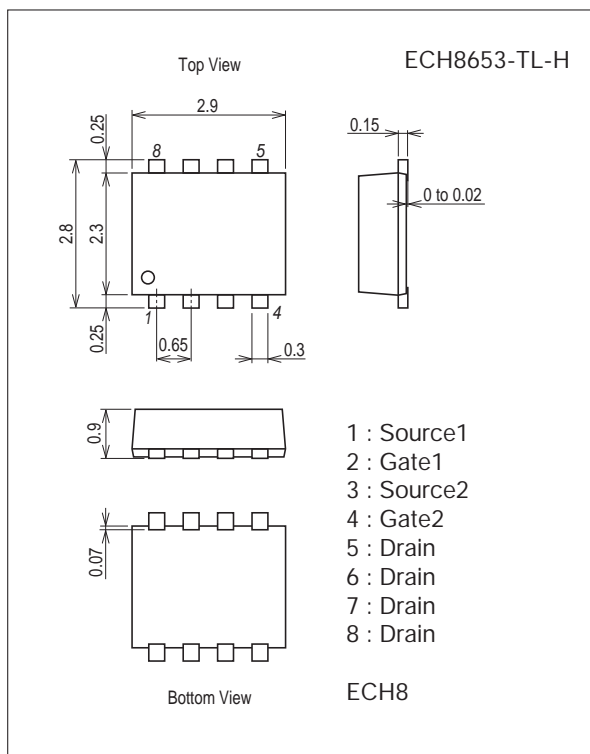
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		7.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.4	W
Total Power Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

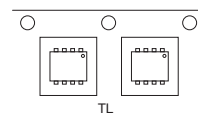
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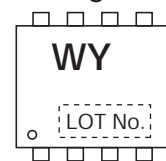
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

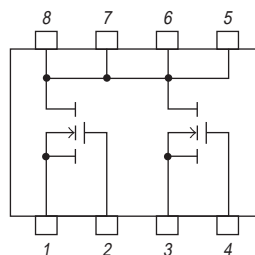
Packing Type : TL



Marking



Electrical Connection

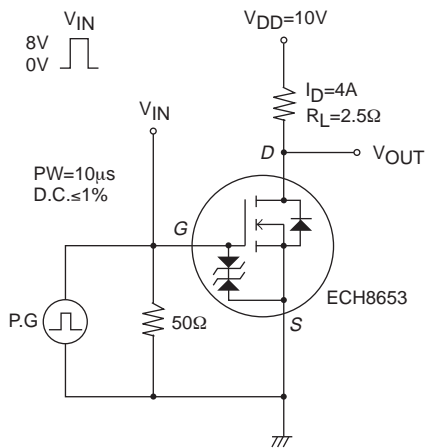


ECH8653

Electrical Characteristics at Ta=25°C

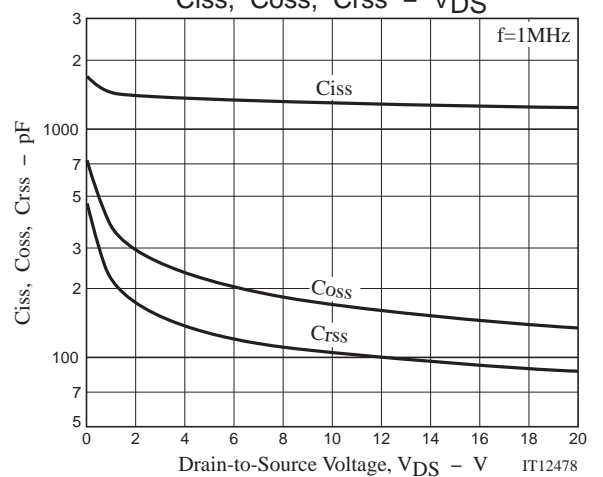
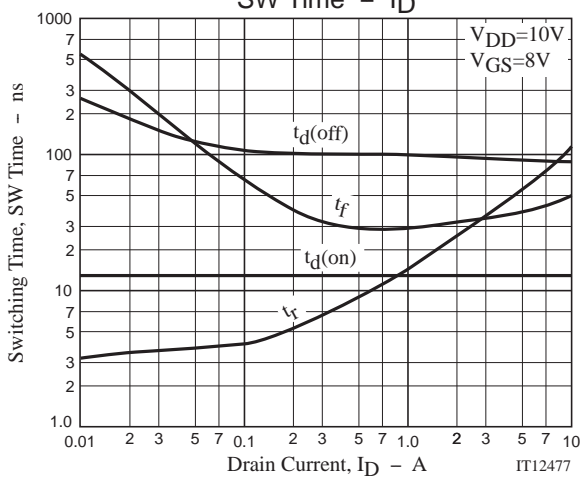
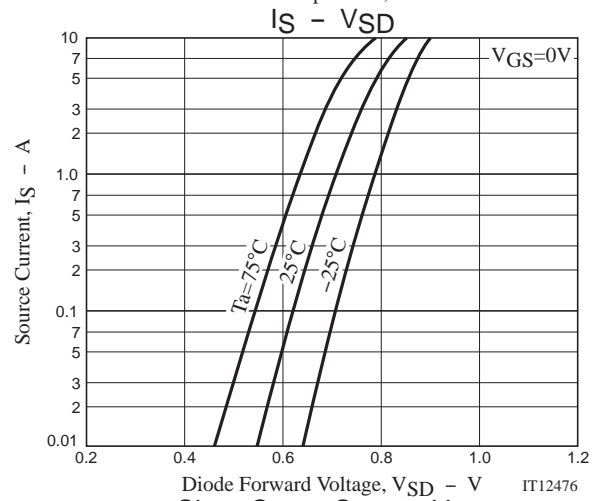
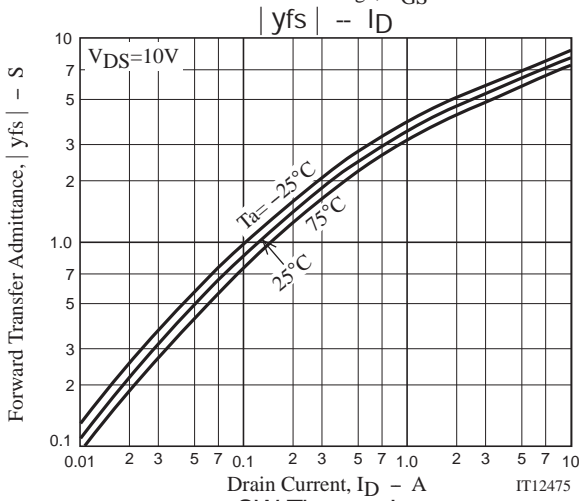
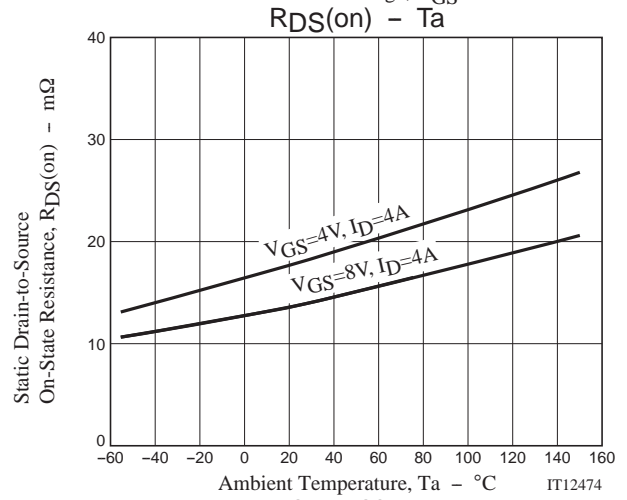
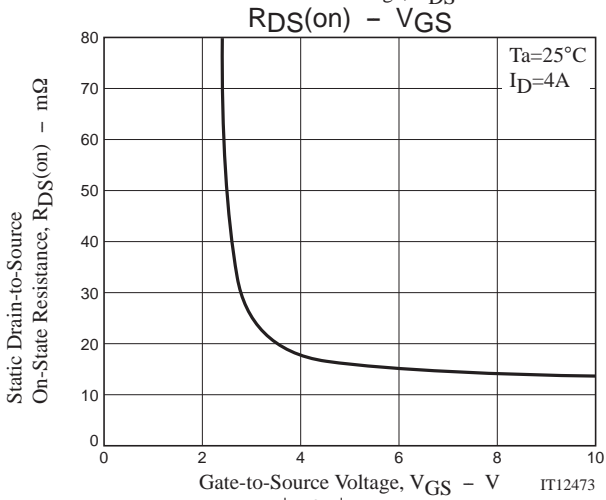
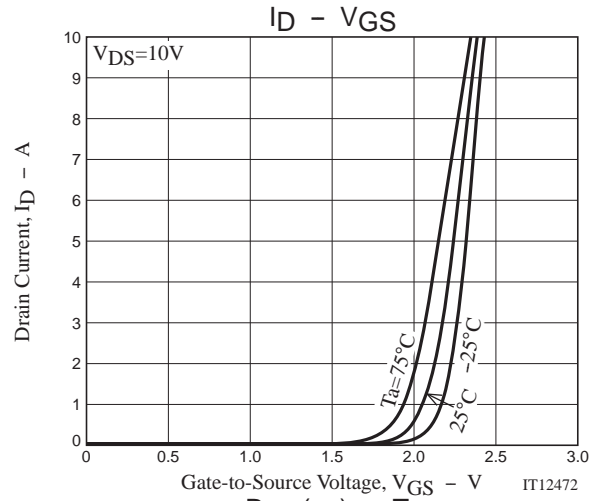
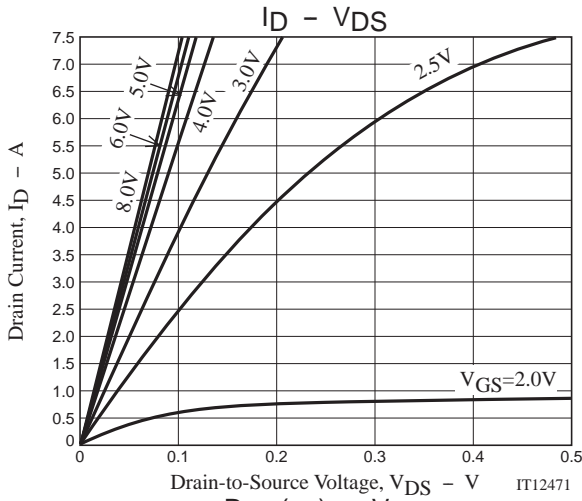
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.0		2.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =4A	3.4	5.8		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =4A, V _{GS} =8V	9	14	20	mΩ
	R _{DS(on)2}	I _D =4A, V _{GS} =4V	11	18	25	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		1280		pF
Output Capacitance	C _{oss}			170		pF
Reverse Transfer Capacitance	C _{rss}			105		pF
Turn-ON Delay Time	t _{d(on)}			13		ns
Rise Time	t _r	See specified Test Circuit.		48		ns
Turn-OFF Delay Time	t _{d(off)}			94		ns
Fall Time	t _f			36		ns
Total Gate Charge	Q _g			18.5		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =10V, V _{GS} =8V, I _D =7.5A		2.7		nC
Gate-to-Drain "Miller" Charge	Q _{gd}			3.1		nC
Diode Forward Voltage	V _{SD}		I _S =7.5A, V _{GS} =0V		0.82	1.2

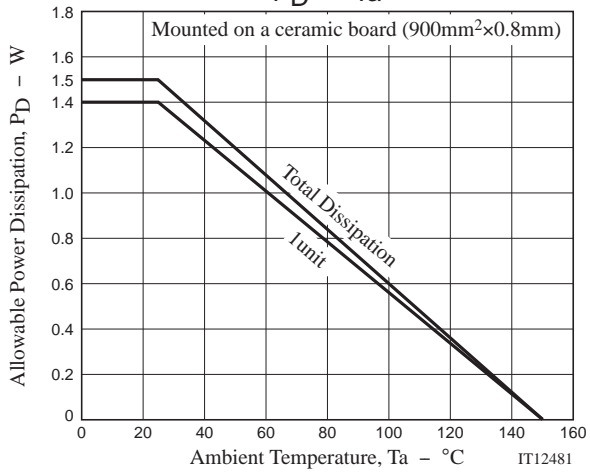
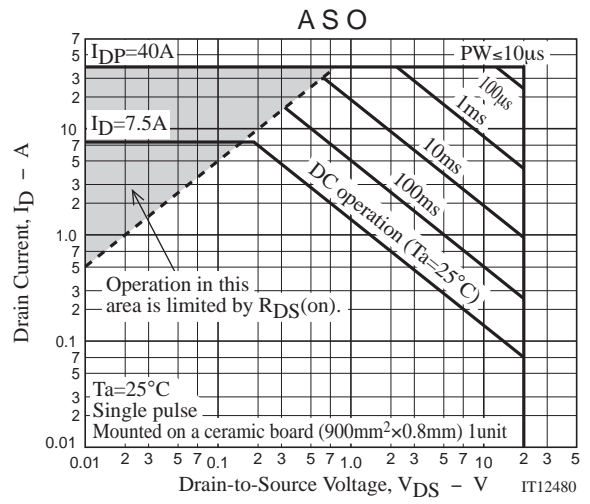
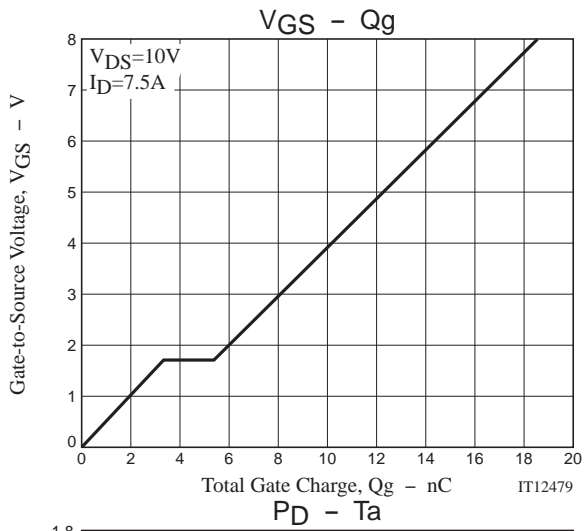
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ECH8653-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free





Embossed Taping Specification

ECH8653-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

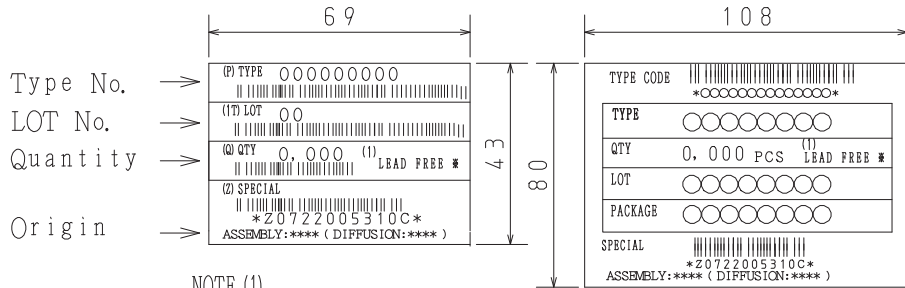
Reel label, Inner box label
(unit :mm)

Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label



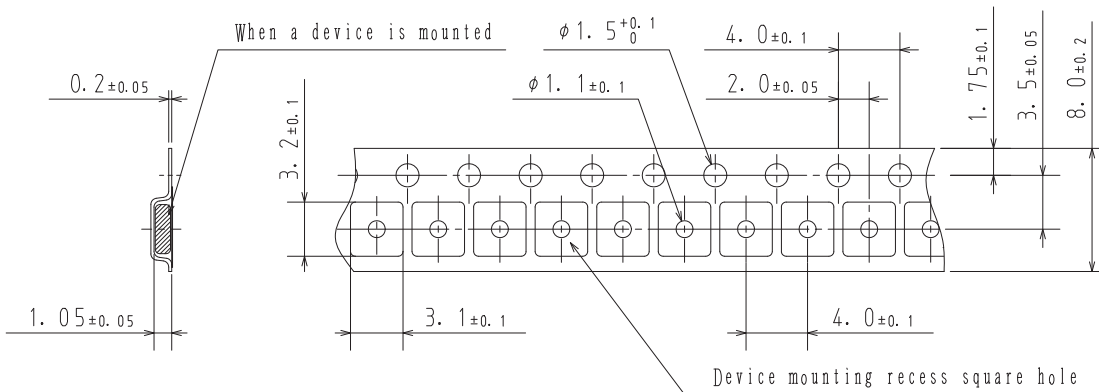
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

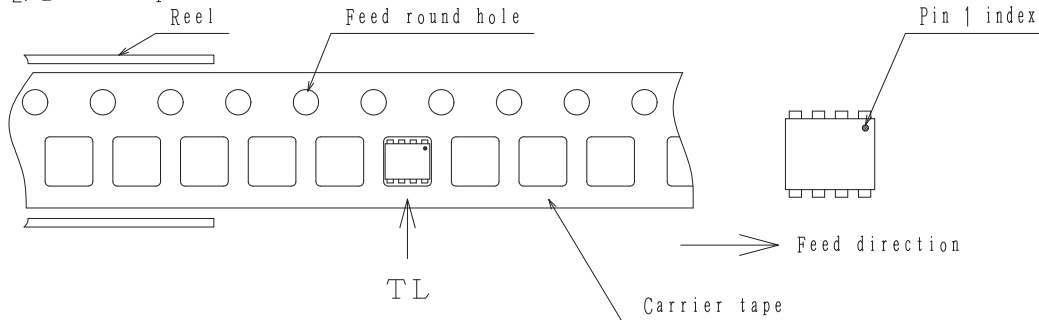
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Those with pin 1 index on the feed hole side.....TL

ECH8653

Outline Drawing ECH8653-TL-H



Land Pattern Example



Note on usage : Since the ECH8653 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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